

CONTENTS

	PAGE
Preface	xi
Chapter 1. INTRODUCTION	1
Chapter 2. CRYSTAL STRUCTURE AND BINDING	5
2.1 Crystal Structure	5
2.1a Properties of the zinc-blende structure	7
2.1b Consequences of lack of inversion symmetry: (111) and (111) faces	8
2.1c Piezoelectric effect	9
2.2 Binding	10
2.2a "Ionicity"	10
2.2b Atomic arrangement	12
2.2c Cleavage	13
2.2d Infra-red lattice absorption	13
2.2e Spin-orbit splitting	18
2.2f Width of the forbidden band	19
2.2g Electronegativity and conclusions on binding	20
2.2h Strength of binding	22
References	25
Chapter 3 BAND STRUCTURE	27
3.1 Introduction: Significance of the Band Structure	27
3.2 Band Structure from Theory	28
3.2a Symmetry	28
3.2b Spin-orbit effects	29
3.2c One-dimensional model	30
3.2d Herman's perturbation method	31
3.3 Cyclotron Resonance and the Diamagnetic Landau Effect	34
3.4 Band Structure of Indium Antimonide	37
3.4a Conduction band	37
3.4b Valence band	45
3.4c Theory	48
3.5 Band Structure of Indium Arsenide	50
3.5a Conduction band	50
3.5b Valence band	51
3.6 Band Structure of Indium Phosphide	52
3.6a Conduction band	52
3.6b Valence band	53
3.7 Band Structure of Gallium Antimonide	54
3.7a Conduction band	54
3.8 Band Structure of Gallium Arsenide	57
3.8a Theory	57
3.8b Conduction band	59
3.8c Valence band	60
3.9 Band Structure of Gallium Phosphide	62
3.10 Band Structure of Aluminium Antimonide	62
3.11 Band Structure of Boron Nitride	63

	PAGE
3.12 Summary of Probable Band Structures of III-V Compounds	64
References	66
Chapter 4 IMPURITIES AND DEFECTS	68
4.1 Introduction	68
4.2 Donors and Acceptors	69
4.2a Hydrogen-like model of impurities	71
4.3 Indium Antimonide	73
4.3a Donor levels	73
4.3b Acceptor levels: impurity band	74
4.4 Indium Arsenide	76
4.5 Indium Phosphide	77
4.6 Gallium Antimonide	77
4.7 Gallium Arsenide	77
4.8 Gallium Phosphide	79
4.9 Aluminium Antimonide	80
4.10 Mixed Crystals	80
4.11 Diffusion	81
4.12 Dislocation Cracks	86
References	86
Chapter 5 PREPARATION	89
5.1 Compound Formation	89
5.2 Purification of the Elements	96
5.3 Methods of Preparation	97
5.4 Apparatus	99
5.4a Indium antimonide	99
5.4b Gallium antimonide	101
5.4c Aluminium antimonide	101
5.4d Indium arsenide	101
5.4e Gallium arsenide	103
5.4f Indium phosphide	104
5.4g Gallium phosphide	106
5.5 Residual Impurities	107
5.6 Floating-Zone Purification	109
References	112
Chapter 6 ELECTRICAL PROPERTIES	114
6.1 Scattering Processes	114
6.1a Lattice scattering by acoustic modes	114
6.1b Lattice scattering by optical modes	115
6.1c Impurity scattering	115
6.1d Carrier-carrier scattering	116
6.1e Mobility in III-V compounds	116
6.2 Carrier Transport Properties	120
6.2a Consequences of a large mobility ratio	120
6.2b Indium antimonide	122
6.2c Indium arsenide	130
6.2d Indium phosphide	134

		PAGE
	6.2e Gallium antimonide	136
	6.2f Gallium arsenide	139
	6.2g Gallium phosphide	144
	6.2h Aluminium antimonide	145
	6.2i Boron phosphide	148
	6.2j Mixed crystals	149
	6.3 Dependence of the Electrical Properties on Magnetic Field	149
	6.3a Indium antimonide	152
	6.3b Indium arsenide	162
	6.3c Gallium arsenide, indium phosphide and aluminium antimonide	163
	References	164
Chapter 7	OPTICAL PROPERTIES AND PHOTOELECTRIC EFFECTS	167
	7.1 Optical Properties	167
	7.1a The absorption edge	168
	7.1b The effects of free carriers	175
	7.1c Lattice absorption	178
	7.1d Refractive index	180
	7.2 Photoelectric Effects	181
	7.2a Recombination mechanisms	181
	7.2b The measurement of carrier lifetime	182
	7.2c Indium antimonide	183
	7.2d Indium arsenide	188
	7.2e Gallium antimonide	189
	7.2f Gallium arsenide	190
	7.2g Other compounds	191
	7.3 Radiation Emission	192
	References	193
Chapter 8	APPLICATIONS	196
	8.1 Junction Applications	197
	8.1a Variable capacitance diodes	199
	8.1b Microwave rectifiers	200
	8.1c Switching diodes	201
	8.1d Tunnel diodes	201
	8.1e Transistors	202
	8.2 Galvanomagnetic Applications	204
	8.2a The Hall effect magnetometer	209
	8.2b The susceptibility meter	211
	8.2c The measurement of electric current and power	211
	8.2d The Hall effect multiplier	214
	8.2e The Hall effect amplifier	216
	8.2f The magnetoresistance oscillator and amplifier	217
	8.2g The magnetoresistance displacement transducer	218
	8.3 Optical Applications	221
	8.3a Infra-red photocells	221
	8.3b Solar batteries	222
	8.3c Optical filters	226
	References	227
	INDEX	231